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# Thyristor High Voltage, Phase Control SCR, 16 A



| PRIMARY CHARACTERISTICS            |                  |  |  |  |  |  |  |
|------------------------------------|------------------|--|--|--|--|--|--|
| I <sub>T(AV)</sub>                 | 10 A             |  |  |  |  |  |  |
| V <sub>DRM</sub> /V <sub>RRM</sub> | 800 V, 1200 V    |  |  |  |  |  |  |
| V <sub>TM</sub>                    | 1.4 V            |  |  |  |  |  |  |
| I <sub>GT</sub>                    | 60 mA            |  |  |  |  |  |  |
| T <sub>J</sub>                     | -40 °C to 125 °C |  |  |  |  |  |  |
| Package                            | TO-220AB 3L      |  |  |  |  |  |  |
| Circuit configuration              | Single SCR       |  |  |  |  |  |  |

#### **FEATURES**

- Designed and qualified according to JEDEC®-JESD 47
- 125 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



#### **APPLICATIONS**

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge

#### **DESCRIPTION**

The VS-16TTS... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operating up to 125 °C junction temperature.

| OUTPUT CURRENT IN TYPICAL APPLICATIONS   |                     |                    |       |  |  |  |  |  |  |
|--|---------------------|--------------------|-------|--|--|--|--|--|--|
| APPLICATIONS   | SINGLE-PHASE BRIDGE | THREE-PHASE BRIDGE | UNITS |  |  |  |  |  |  |
| Capacitive input filter T <sub>A</sub> = 55 °C, T <sub>J</sub> = 125 °C, common heatsink of 1 °C/W | 13.5                | 17                 | А     |  |  |  |  |  |  |

| MAJOR RATINGS AND CHARACTERISTICS  |                              |             |       |  |  |  |  |  |  |  |
|------------------------------------|------------------------------|-------------|-------|--|--|--|--|--|--|--|
| PARAMETER                          | TEST CONDITIONS              | VALUES      | UNITS |  |  |  |  |  |  |  |
| I <sub>T(AV)</sub>                 | Sinusoidal waveform          | 10          | A     |  |  |  |  |  |  |  |
| I <sub>RMS</sub>                   |                              | 16          | A     |  |  |  |  |  |  |  |
| V <sub>DRM</sub> /V <sub>RRM</sub> | Range (1)                    | 800, 1200   | V     |  |  |  |  |  |  |  |
| I <sub>TSM</sub>                   |                              | 200         | А     |  |  |  |  |  |  |  |
| V <sub>T</sub>                     | 10 A, T <sub>J</sub> = 25 °C | 1.4         | V     |  |  |  |  |  |  |  |
| dV/dt                              |                              | 500         | V/µs  |  |  |  |  |  |  |  |
| dl/dt                              |                              | 150         | A/µs  |  |  |  |  |  |  |  |
| T <sub>J</sub>                     | Range                        | -40 to +125 | °C    |  |  |  |  |  |  |  |

#### Note

(1) For higher voltage up to 1600 V contact factory

| VOLTAGE RATINGS |   |  |   |  |  |  |  |  |  |  |
|-----------------|---|--|---|--|--|--|--|--|--|--|
| PART NUMBER     | V <sub>RRM</sub> , MAXIMUM PEAK<br>REVERSE VOLTAGE<br>V | V <sub>DRM</sub> , MAXIMUM PEAK<br>DIRECT VOLTAGE<br>V | I <sub>RRM</sub> /I <sub>DRM</sub><br>AT 125 °C<br>mA |  |  |  |  |  |  |  |
| VS-16TTS08-M3   | 800   | 800  | 10  |  |  |  |  |  |  |  |
| VS-16TTS12-M3   | 1200  | 1200   | 10  |  |  |  |  |  |  |  |

# VS-16TTS08-M3, VS-16TTS12-M3

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| ABSOLUTE MAXIMUM RATINGS                   |                    |   |   |       |   |                  |    |  |
|--|--------------------|---|---|-------|---|------------------|----|--|
| PARAMETER                                  | SYMBOL             |   | VAL   | UNITS |   |                  |    |  |
| PARAMETER                                  | STINIBUL           |   | TEST CONDITIONS   | TYP.  | UNITS   |                  |    |  |
| Maximum average on-state current           | I <sub>T(AV)</sub> | T <sub>C</sub> = 98 °C, 1   | 80° conduction, half sine wave  | 1     | 0   |                  |    |  |
| Maximum RMS on-state current               | I <sub>RMS</sub>   |   |   | 1     | 6   | Α                |    |  |
| Maximum peak, one-cycle,                   | L                  | 10 ms sine p  | ulse, rated V <sub>RRM</sub> applied  | 1     | 70  |                  |    |  |
| non-repetitive surge current               | I <sub>TSM</sub>   | 10 ms sine p  | ulse, no voltage reapplied  | 20    | 00  |                  |    |  |
| Maximum I <sup>2</sup> t for fusing        | l <sup>2</sup> t   | 10 ms sine p  | ulse, rated V <sub>RRM</sub> applied  | 144   |   | A <sup>2</sup> s |    |  |
| waximum i-t for fusing                     | 1-1                | 10 ms sine p  | 200   |       | A-S   |                  |    |  |
| Maximum I <sup>2</sup> √t for fusing       | I <sup>2</sup> √t  | t = 0.1 to 10 r   | ns, no voltage reapplied  | 2000  |   | A²√s             |    |  |
| Maximum on-state voltage drop              | $V_{TM}$           | 10 A, T <sub>J</sub> = 25   | °C  | 1.4   |   | V                |    |  |
| On-state slope resistance                  | r <sub>t</sub>     | T <sub>.1</sub> = 125 °C  | Z4.0  |       | 1.0   | mΩ               |    |  |
| Threshold voltage                          | V <sub>T(TO)</sub> | 1j=125 C  |   | 1.1   |   | V                |    |  |
| Maximum reverse and direct leakage current | 1 /1               | T <sub>J</sub> = 25 °C  | V - Botod V A   | 0.5   |   |                  |    |  |
| waximum reverse and unect leakage current  | $I_{RM}/I_{DM}$    | T <sub>J</sub> = 125 °C   | $V_R = Rated V_{RRM}/V_{DRM}$   | 10    |   |                  |    |  |
| Holding current                            | l <sub>Η</sub>     | Anode supply = 6 V, resistive load, initial $I_T$ = 1 A 16TTS08PbF, 16TTS12PbF, $T_J$ = 25 °C |   | -     | 150   | mA               |    |  |
| Maximum latching current                   | IL                 | Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C                                    |   |       | $I_L$ Anode supply = 6 V, resistive load, $T_J = 25$ °C 200 |                  | 00 |  |
| Maximum rate of rise of off-state voltage  | dV/dt              | $T_J = T_J \text{ max.},$   | $T_J = T_J \text{ max., linear to } 80 ^{\circ}\text{C}, V_{DRM} = R_g - k = \text{Open}$ |       |   | V/µs             |    |  |
| Maximum rate of rise of turned-on current  | dI/dt              |   |   | 150   |   | A/µs             |    |  |

| TRIGGERING                                  |                   |  |        |       |  |
|---|-------------------|--|--------|-------|--|
| PARAMETER                                   | SYMBOL            | TEST CONDITIONS  | VALUES | UNITS |  |
| Maximum peak gate power                     | P <sub>GM</sub>   |  | 8.0    | W     |  |
| Maximum average gate power                  | $P_{G(AV)}$       |  | 2.0    | VV    |  |
| Maximum peak positive gate current          | + I <sub>GM</sub> |  | 1.5    | Α     |  |
| Maximum peak negative gate voltage          | - V <sub>GM</sub> |  | 10     | V     |  |
|   |                   | Anode supply = 6 V, resistive load, T <sub>J</sub> = - 65 °C | 90     | 1     |  |
| Maximum required DC gate current to trigger | $I_{GT}$          | Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C   | 60     | mA    |  |
|   |                   | Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C  | 35     |       |  |
|   |                   | Anode supply = 6 V, resistive load, T <sub>J</sub> = - 65 °C | 3.0    |       |  |
| Maximum required DC gate voltage to trigger | $V_{GT}$          | Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C   | 2.0    | v     |  |
| voltage to alleger                          |                   | Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C  | 1.0    | V     |  |
| Maximum DC gate voltage not to trigger      | $V_{GD}$          | /GD T 105 °C V Dated value                                   |        |       |  |
| Maximum DC gate current not to trigger      | I <sub>GD</sub>   | T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = Rated value      | 2.0    | mA    |  |

| SWITCHING                     |                 |                         |        |       |  |  |  |  |
|-------------------------------|-----------------|-------------------------|--------|-------|--|--|--|--|
| PARAMETER                     | SYMBOL          | TEST CONDITIONS         | VALUES | UNITS |  |  |  |  |
| Typical turn-on time          | t <sub>gt</sub> | T <sub>J</sub> = 25 °C  | 0.9    |       |  |  |  |  |
| Typical reverse recovery time | t <sub>rr</sub> | T. – 105 °C             | 4      | μs    |  |  |  |  |
| Typical turn-off time         | tq              | T <sub>J</sub> = 125 °C | 110    |       |  |  |  |  |

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| THERMAL AND MECHANICAL SPECIFICATIONS           |         |                                   |                                      |             |                  |  |  |  |
|---|---------|-----------------------------------|--------------------------------------|-------------|------------------|--|--|--|
| PARAMETER                                       |         | SYMBOL                            | TEST CONDITIONS                      | VALUES      | UNITS            |  |  |  |
| Maximum junction and storage temperature range  |         | T <sub>J</sub> , T <sub>Stg</sub> |                                      | -40 to +125 | °C               |  |  |  |
| Maximum thermal resistance, junction to case    |         | $R_{thJC}$                        | DC operation                         | 1.3         |                  |  |  |  |
| Maximum thermal resistance, junction to ambient |         | R <sub>thJA</sub>                 |                                      | 62          | °C/W             |  |  |  |
| Typical thermal resistance, case to heatsink    | tance,  |                                   | Mounting surface, smooth and greased | 0.5         |                  |  |  |  |
| Approximate weight                              |         |                                   |                                      | 2           | g                |  |  |  |
| Approximate weight                              |         |                                   |                                      | 0.07        | OZ.              |  |  |  |
| Mounting torque                                 | minimum |                                   |                                      | 6 (5)       | kgf · cm         |  |  |  |
| Mounting torque                                 | maximum |                                   |                                      | 12 (10)     | (lbf $\cdot$ in) |  |  |  |
| Mayling daving                                  |         |                                   | Coop at the TO 200AR SI              | 16TTS08     |                  |  |  |  |
| Marking device                                  |         |                                   | Case style TO-220AB 3L               | 16TTS12     |                  |  |  |  |

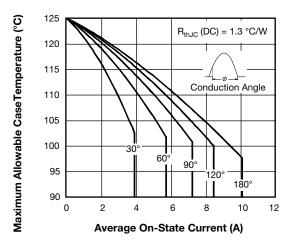


Fig. 1 - Current Rating Characteristics

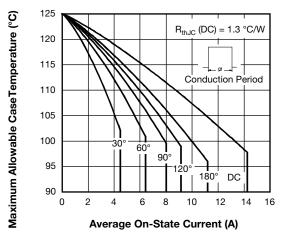


Fig. 2 - Current Rating Characteristics

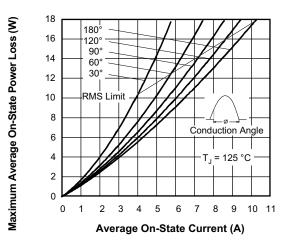


Fig. 3 - On-State Power Loss Characteristics

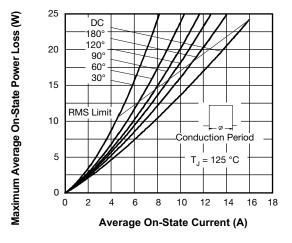


Fig. 4 - On-State Power Loss Characteristics



Peak Half Sine Wave On-State Current (A)

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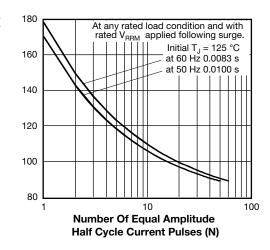


Fig. 5 - Maximum Non-Repetitive Surge Current

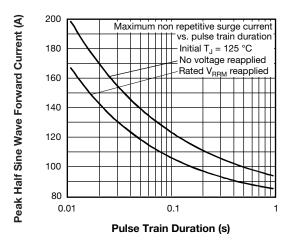


Fig. 6 - Maximum Non-Repetitive Surge Current

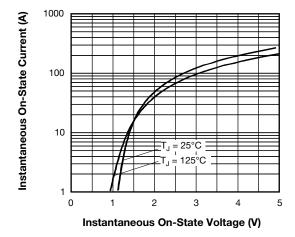


Fig. 7 - On-State Voltage Drop Characteristics

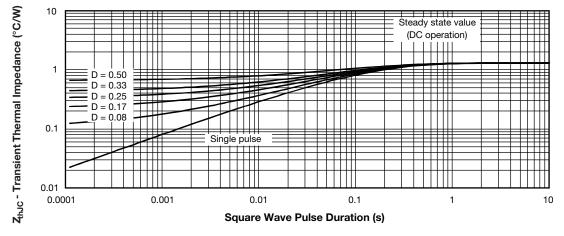


Fig. 8 - Thermal Impedance Z<sub>thJC</sub> Characteristics

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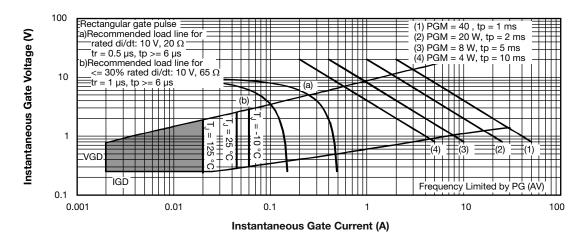


Fig. 9 - Gate Characteristics

### **ORDERING INFORMATION TABLE**

**Device code** 

| 1                 | 2           | 3                        | 4               | 5 | 6    | 7                  |  |  |
|-------------------|-------------|--------------------------|-----------------|---|------|--------------------|--|--|
| 1 -<br>2 -<br>3 - | Cur<br>Circ | ent ratir                | guration        | · | duct |                    |  |  |
| 4 -               | Pac         | kage:<br>TO-220 <i>i</i> | -               |   |      |                    |  |  |
| 5 -               |             | e of silic               | on:<br>er grade |   | _    |                    |  |  |
| 6 -<br>7 -        | Volt        |                          | e x 100         |   |      | 08 = 80<br>12 = 12 |  |  |

| ORDERING INFORMATION (Example)                    |    |                          |  |  |  |  |  |
|---|----|--------------------------|--|--|--|--|--|
| PREFERRED P/N BASE QUANTITY PACKAGING DESCRIPTION |    |                          |  |  |  |  |  |
| VS-16TTS08-M3                                     | 50 | Antistatic plastic tubes |  |  |  |  |  |
| VS-16TTS12-M3                                     | 50 | Antistatic plastic tubes |  |  |  |  |  |

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

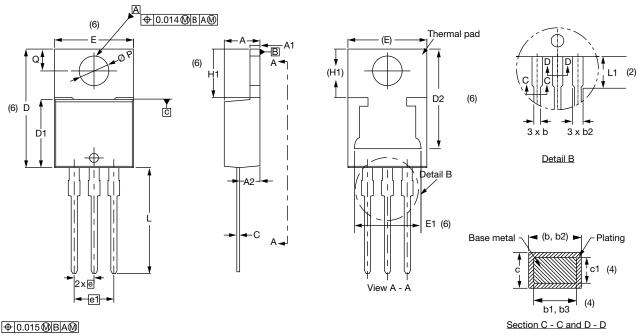
| LINKS TO RELATED DOCUMENTS |                          |  |  |  |  |  |
|----------------------------|--------------------------|--|--|--|--|--|
| Dimensions                 | www.vishay.com/doc?96154 |  |  |  |  |  |
| Part marking information   | www.vishay.com/doc?95028 |  |  |  |  |  |

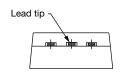


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### **TO-220AB 3L**

#### **DIMENSIONS** in millimeters and inches





Conforms to JEDEC® outline TO-220AB

| SYMBOL | MILLIM | IETERS | INC   | HES   | NOTES | NOTES |          | TES SYMBOL |       | MILLIMETERS |       | INCHES |  | NOTES |
|--------|--------|--------|-------|-------|-------|-------|----------|------------|-------|-------------|-------|--------|--|-------|
| STMBOL | MIN.   | MAX.   | MIN.  | MAX.  | NOTES | NOTES | STIVIBOL | MIN.       | MAX.  | MIN.        | MAX.  | NOTES  |  |       |
| Α      | 4.25   | 4.65   | 0.167 | 0.183 |       |       | D2       | 11.68      | 13.30 | 0.460       | 0.524 | 6, 7   |  |       |
| A1     | 1.14   | 1.40   | 0.045 | 0.055 |       |       | Е        | 10.11      | 10.51 | 0.398       | 0.414 | 3, 6   |  |       |
| A2     | 2.50   | 2.92   | 0.098 | 0.115 |       |       | E1       | 6.86       | 8.89  | 0.270       | 0.350 | 6      |  |       |
| b      | 0.69   | 1.01   | 0.027 | 0.040 |       |       | е        | 2.41       | 2.67  | 0.095       | 0.105 |        |  |       |
| b1     | 0.38   | 0.97   | 0.015 | 0.038 | 4     |       | e1       | 4.88       | 5.28  | 0.192       | 0.208 |        |  |       |
| b2     | 1.20   | 1.73   | 0.047 | 0.068 |       |       | H1       | 6.09       | 6.48  | 0.240       | 0.255 | 6      |  |       |
| b3     | 1.14   | 1.73   | 0.045 | 0.068 | 4     |       | L        | 13.52      | 14.02 | 0.532       | 0.552 |        |  |       |
| С      | 0.36   | 0.61   | 0.014 | 0.024 |       |       | L1       | 3.32       | 3.82  | 0.131       | 0.150 | 2      |  |       |
| c1     | 0.36   | 0.56   | 0.014 | 0.022 | 4     |       | ØΡ       | 3.54       | 3.91  | 0.139       | 0.154 |        |  |       |
| D      | 14.85  | 15.35  | 0.585 | 0.604 | 3     |       | Q        | 2.60       | 3.00  | 0.102       | 0.118 |        |  |       |
| D1     | 8.38   | 9.02   | 0.330 | 0.355 |       |       |          |            |       |             |       |        |  |       |

### **Notes**

- <sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3, and c1 apply to base metal only
- Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2, and E1
- (7) Outline conforms to JEDEC® TO-220, except D2



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